

### 描述 / Descriptions

TO-92LM 塑封封装 PNP 半导体三极管。Silicon PNP transistor in a TO-92LM Plastic Package.

### 特征 / Features

高击穿电压,小反向传输电容,高频特性好。

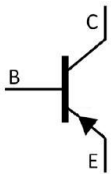
High breakdown voltage, small reverse transfer capacitance and excellent high frequency characteristic.

### 用途 / Applications

用于彩电行输出和高击穿电压驱动。

Color TV chrome output and high breakdown voltage driver.

### 内部等效电路 / Equivalent Circuit



### 引脚排列 / Pinning



PIN 1 : Base      PIN 2 : Collector      PIN 3 : Emitter

### 放大及印章代码 / $h_{FE}$ Classifications & Marking

$h_{FE}$ Classifications Symbol	C	D	E	F
$h_{FE}$ Range	40~80	60~120	100~200	160~320

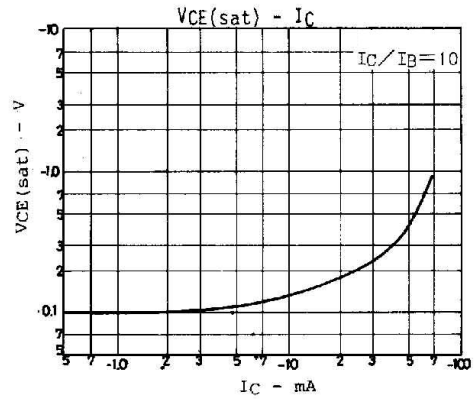
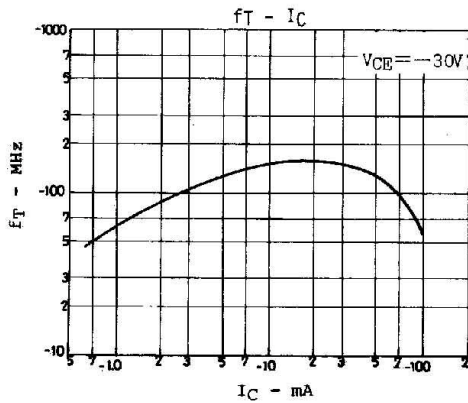
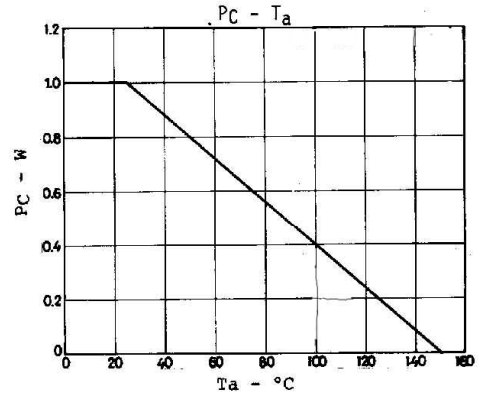
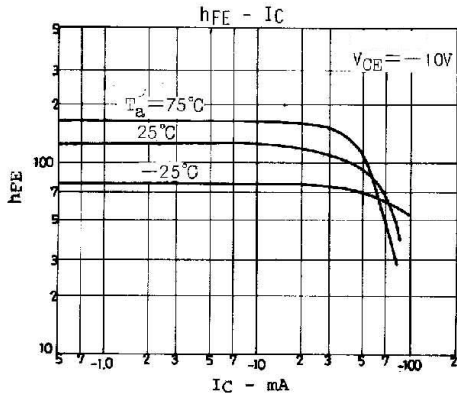
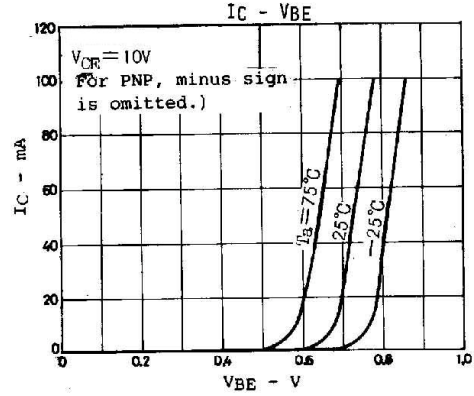
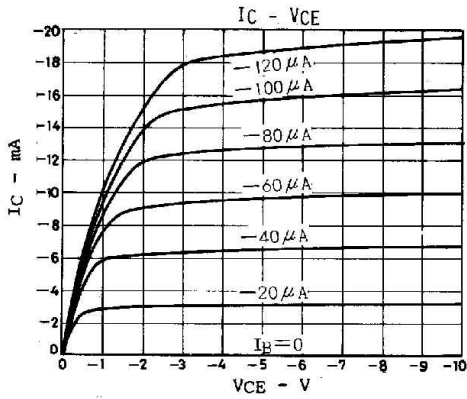
**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	$V_{CBO}$	-200	V
Collector to Emitter Voltage	$V_{CEO}$	-200	V
Emitter to Base Voltage	$V_{EBO}$	-5.0	V
Collector Current - Continuous	$I_C$	-100	mA
Collector Current – Continuous(Pulse)	$I_{CP}$	-200	mA
Collector Power Dissipation	$P_C$	1.0	W
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C

**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	$V_{CBO}$	$I_C=-10\mu A$ $I_E=0$	-200			V
Collector to Emitter Breakdown Voltage	$V_{CEO}$	$I_C=-1.0mA$ $R_{BE}=\infty$	-200			V
Emitter to Base Breakdown Voltage	$V_{EBO}$	$I_E=-10\mu A$ $I_C=0$	-5.0			V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=-150V$ $I_E=0$			-0.1	$\mu A$
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB}=-4.0V$ $I_C=0$			-0.1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE}=-10V$ $I_C=-10mA$	40		320	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-20mA$ $I_B=-2.0mA$			-0.6	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-20mA$ $I_B=-2.0mA$			-1.0	V
Transition Frequency	$f_T$	$V_{CE}=-30V$ $I_C=-10mA$		150		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-30V$ $f=1.0MHz$		2.6		pF
Reverse Transfer Capacitance	$C_{re}$	$V_{CB}=-30V$ $f=1.0MHz$		1.7		pF

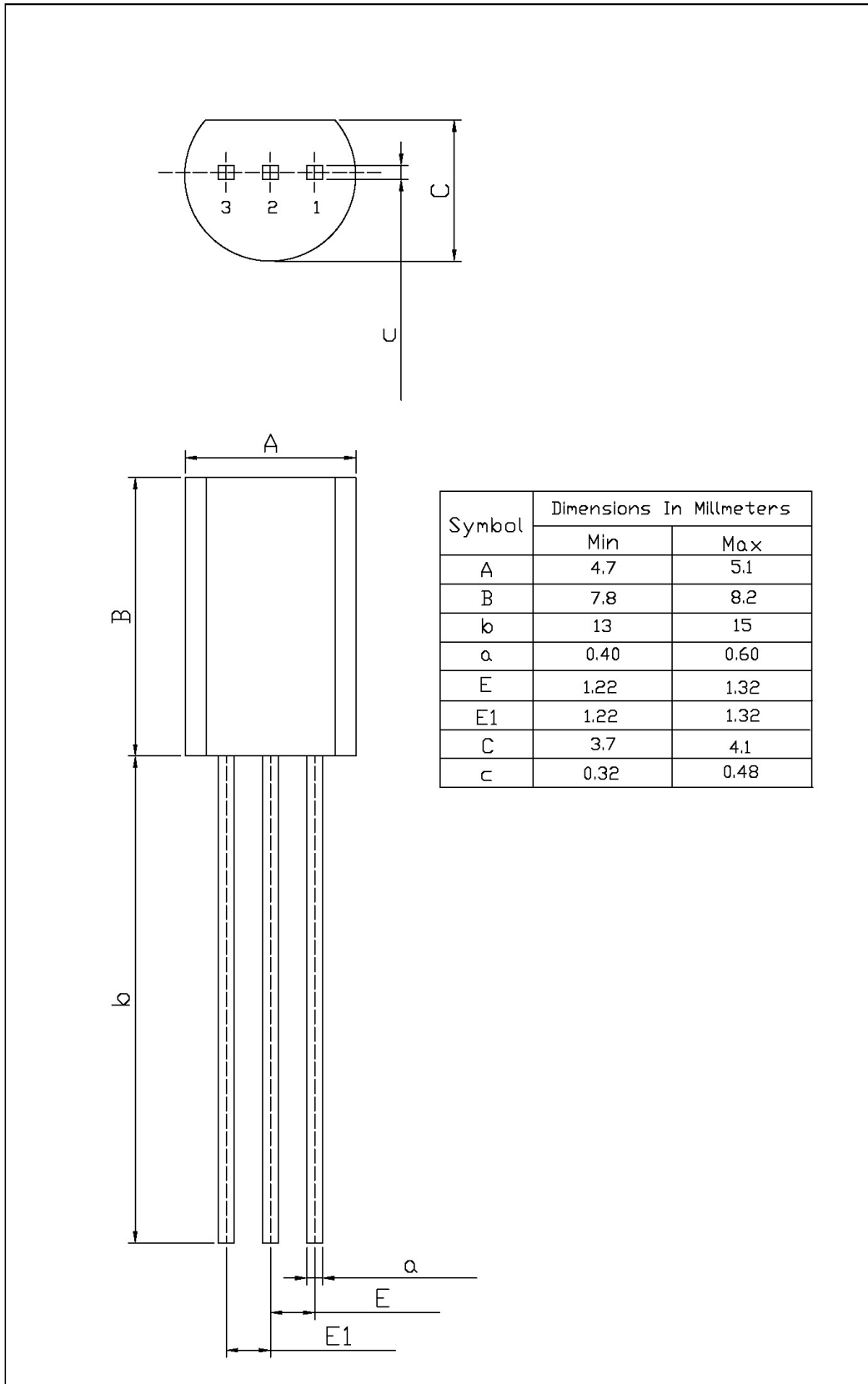
电参数曲线图 / Electrical Characteristic Curve



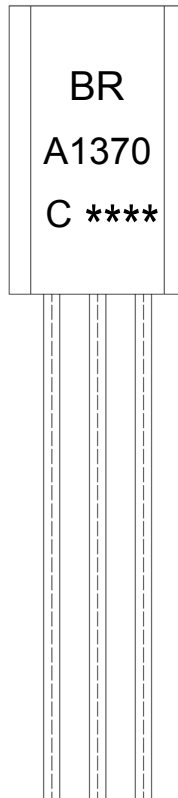
外形尺寸图 / Package Dimensions

T0-92LM

Unit: mm



印章说明 / Marking Instructions



说明：

BR: 为公司代码

A1370 : 为型号代码

C: 为  $h_{FE}$  分档代码

\*\*\*\* : 为生产批号代码，随生产批号变化。

Note:

BR: Company Code.

A1370: Product Type.

C:  $h_{FE}$  Classifications Symbol

\*\*\*\*: Lot No. Code, code change with Lot No.

**波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)**



说明：

- 1、预热温度 25~150°C，时间 60~90sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：270±5°C      时间：10±1 sec.      Temp.:270±5°C      Time:10±1 sec

**包装规格 / Packaging SPEC.**

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-92LM	1,000	8	8,000	5	40,000	135×190	237×172×102	560×245×195

编带包装 / AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	Units/tape 只/纸带	Tape/Inner Box 纸带/盒	Rows/Inner Box 纸带层/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Inner Box 盒	Outer Box 箱
TO-92LM	2,500	1	100	10	25,000	328×230×42	小箱 480×346×235 大箱 547×407×268

**使用说明 / Notices**